

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1476** is a planar transistor using diffused emitter ballasted resistors for high linearity Class AB operation in VHF and band 1 television transmitters and transposers.

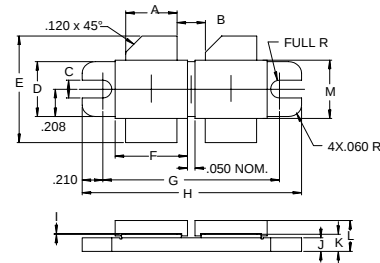
FEATURES:

- Common Emitter
- $P_G = 12$ dB at 240 W/88 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	25 A
V_{CBO}	70 V
V_{CEO}	40 V
V_{EBO}	4.0 V
P_{DISS}	430 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.4°C/W

PACKAGE STYLE .450 BAL FLG(B)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.373 / 9.47	.385 / 9.78
B	.205 / 5.21	
C	.120 / 3.25	.130 / 3.30
D	.411 / 10.44	.421 / 10.69
E	.825 / 20.96	.865 / 21.97
F	.525 / 13.34	.535 / 13.59
G	1.255 / 31.88	1.265 / 32.18
H	1.675 / 42.55	1.685 / 42.80
I	.002 / 0.05	.006 / 0.15
J	.095 / 2.41	.105 / 2.67
K	.115 / 2.92	.135 / 3.43
L		.250 / 6.35
M	.445 / 11.30	.457 / 11.61

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 50$ mA	70			V
BV_{CEO}	$I_C = 100$ mA	40			V
BV_{EBO}	$I_E = 20$ mA	4.0			V
I_{CEO}	$V_{CE} = 30$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 7.0$ A	10		50	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			220	pF
P_G	$V_{CE} = 32$ V $I_C = 2 \times 400$ mA $f = 88$ MHz	12			dB
η_C	$P_{OUT} = 240$ W	50			%